JAGIELSKI, J.; NOLIS, J.; ROBACZYNSKA, G.

Electrocardiogram of the newborn infant. Kardiol. Pol. 7 no.2:87-96 164.

1. Z Osrodka Kardiologicznego PSK nr 1 (Kierownik: prof, dr Z. Kowarzykowa) i z I Kliniki Poloznictwa i Chorob Kobiecych Akademii Medycznej we Wroclawiu (Kierownik: prof. dr K. Nowosad).

NOWOGAD, Kazimierz; NoLIS, Jadwigs; ROBACZYNSKA, Gebriels; CIASTON-MALOIFFIZA, Mercuika; KROL, Liitanu; BARON, Adam

Treatment of nechacal hemolytic disease by means of exchange blood transfusions in the past 15 years (1949-1964). Ginek. Fol. 36 no.8:847-852 Ag 165.

1. 2 I Kliniki Foloznistwa i Cherob Kobisoych Akademii Medycznej we Broslawia (Kierownika prof. dr. med. K. Nowesed).

"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137

KOWAREYK, Hogon; KOWERZYROWE, to fin; NOWCEAD, Manisters; MAGIELSKI, Jozef; NOLIS, Jenwige; USEC, Mischyales

The problem of vectors and ographic investigations in the neuboins. Givek. Pol. 36 ne.8:830890 bg tot.

1. 2 Obrodka Karatologiernem FF6 Nr.) we We Hawia (Kieromik: prof. dr. med. 2. Kowarzykowa) i z l hijniki Poloznistwa i Choreb Kobiecych Akademii Medycznoj we Wroclariu (Kierownik: prof. dr. med. K. Nowosaa).

"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137.

JAGELSKI, Jonef; Rollsowa, Jadwiga

Axoncardiograms of the QRS complex in newborn twins. Since led.
36 no.8:691-296 Fg '65.

1. Z. Osrodka Kardiologicznago przy PSK Br. 1 ws Wrzelsziu (Kierownik: prof. dr. med. Z. Kozarcykova) i z I Miniti Polomietza i Chorob Kobiecych Akademii Nadycznej we Wrzelsziu (Kierownik: prof. dr. med. K. Koyosad).

ANDREASIK, Zbigniew; ANDREASIK, Irena; DZIFRZKOMA, Wanda; ROLISOWA, Jadwiga

Recurrent jaundice in the course of pregnancy. Ginek. Fol. 36 nc.8: 931-934 Ag 165.

1. Z II Kliniki Chcrob Wewnetrznych Akademii Mcdycznej we Wrocławiu (Kierownik: prof. dr. med. A. Falkiewicz), z I Kliniki Poloznictwa i Chorob Kobiecych Akademii Medycznej we Wrocławiu (Kierownik: prof. dr. med. K. Nowosad) i z Pracowni Serologicznej Wojewodzkiej Stacji Krwiodawstwa we Wrocławiu (Kierownik: dr. med. W. Dzierzkowa).

NOWOSAD, Kazimierz; HEIMMATH, Tadeusz; MOLISOMA, Jadwiga; CIASTON-MAIOLEPSZA Weronika

Role of listeriosis in pregnancy complications and its spreading in wards for newborn infants. Ginek. Pol. 36 no.8:939-944 Ag '64.

1. Z I Kliniki Poloznictwa i (horob Kobiecych Akademii Medycznej we Wrocławiu (Kierownik: prof. dr. med. K. Nowosad).

HEINEATH, Tadouse: HOLIS, Tasios

Premature separation of normally located placents. Afibringenemia.
Case report. Foleki tygod.lek. 15 no.33:1280-1282 15 Ag '60.

1. Z I Kliniki Foloznictwa i Chorob Kobiecych A.W. we Wroclawiu;
kierownik: doc. dr Lazimiers Howosad.
(PLACENTA PRABVIA blood)
(AFIBRINGGENEMIA in pregn.)

ROBACZINSKI, Jerzy; NOLIS, Tasios

Damage to the fetal extremities caused by encirclement by the umbilical cord. Ginek. pol. 34 no.4:519-523 163.

1. Z I Kliniki Poloznictwa i Chorob Kobiecych AM we Wroclawiu Kierownik: prof. dr med. K. Nowosad.

(UMBILICAL CORD) (EXTREMITIES)

(ABNORMALITIES) (FETAL DISEASES)

(INFANT, NEWBORN, DISEASES)

NOWOSAD, Kazimierz, prof. dr.; WAWRZKIEWICZ, Marian; NOLIS, Tasica; WIECZOREK, Eligiusz.

Con cribution to the clinical picture of preinvasive cancer of the uterine cervix. Pol. tyg. lek. 20 no.12:434-436 22 Mr 165

1. Z I Kliniki Poloznictwa i Chorob Kobiecych Akademii Medycznej we Wroclawiu (Kierownik: prof. dr. K. Nowosed).

WAWRZKIEWICZ, Marian; NOLIS, Tasios

Invasive cervical cancer in pregnant women. Pol. tyg. lek. 20 no.20:721-723 17 My '65.

1. Z Kliniki Poloznictwa i Chorob Kobiecych AM we Wrocławiu (Kierownik: porf. dr. K. Nowos d).

NOLIS, Tasios; NOLISUMA, Jadwiga

Umbilical infections of newborn infants. Ginek. Pol. 36 no.8:
897-901 Ag '65.

1. Z I Kliniki Poloznictwa i Chorob Kobiecych Akademii Medycznej
we Wroblawiu (Kierawnik: prof. dr. med. K. Nowosad).

GIERON-ZASADZIENIOWA, M.; HALAZINSKA, L.; NOLISOWA, J.; UJEC, M.; ROBACZYNSKA, G.; JAGIELSKI, J.

Auricular pararhythm in newborn 'nfants. Kardiol. Pol. 7 no.3:211-216 J '64.

1. Z II Kliniki Poloznictwa i Chorob Kobiecych Akademii Medycznej (Kierownik: prof. dr K. Jablonski); z I Kliniki Poloznictwa i Chorob Kobiecych Akademii Medycznej (Kierownik: prof. dr K. Nowosad) i z Osrodka Kardiologicznego PSK nr l we Wroclawiu (Kierownik: prof. dr Z. Kowarzykowa).

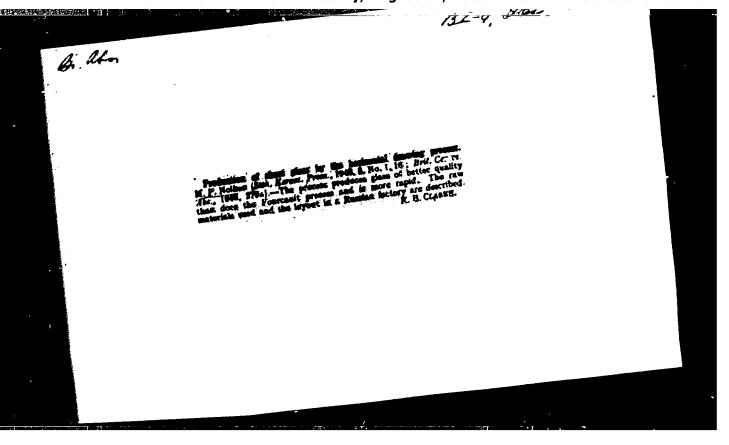
"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137.

Wolls, Tasios; Molischia, Jadwiga

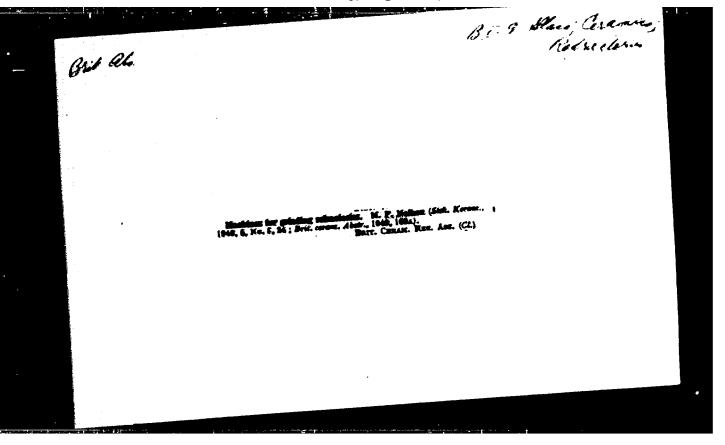
Umbilical infections of newborn infants. Ginek. Pol. 36 no.8:
897-901 Ag '65.

1. Z I Kliniki Poloznictwa i Choron Kobiecych Akademii Medycznej
we Wrowlawiu (Kierownik: prof. dr. med. K. Nowcead).

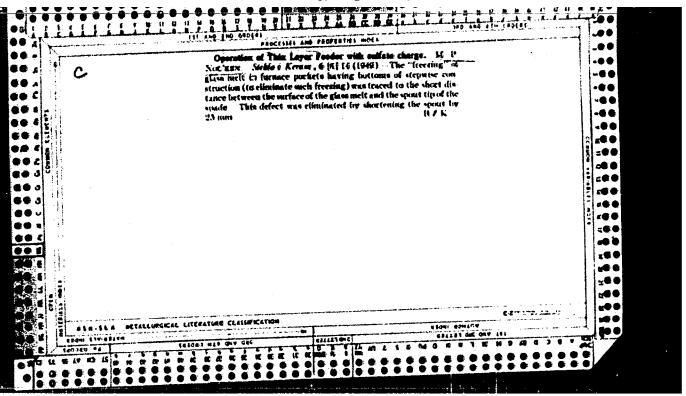
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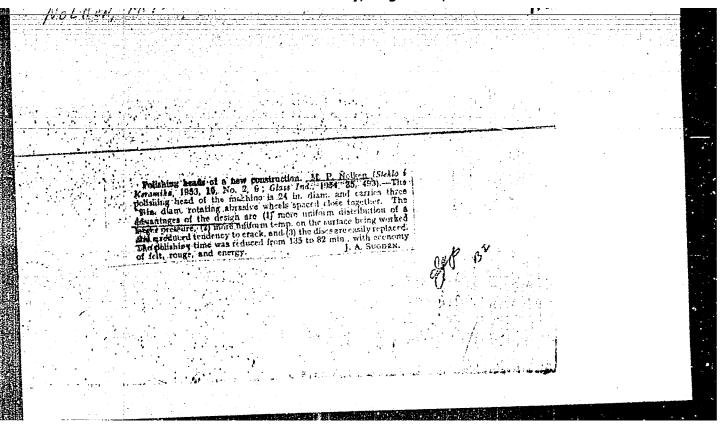
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"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137



AUTHOR: Hol'ken, M. P. 504/72-58-9-3/20

TITLE: Experience in the Introduction of Simultaneous Bilateral Grinding of Sheet Glass (Iz opyta esvoyeniya odnovremennoy

dvusteronney shlifovki listovogo stekla)

PERIODICAL: Steklo i keramika, 1958, Nr 9, pp 7 - 12 (USSR)

ABSTRACT: This method of glass grinding effers considerable

advantages as compared to a separate working of each glass surface. It permits to save working space and equipment and to produce high-quality glass. In order to solve the problem which are connected with this method a small continuous test plant was constructed in glass works. This plant operated according to the system due to Ya.I.Andrusenko and M.D.Tamarin. It was designed in the Orgsteklo (PKB, Institute of Glass). The designs of the grinding machines of this system are portrayed in figures 1,2 and 3. Ya.I.Andrusenko

suggested a hydraulic pulse generator for the stabilisation of the level of the system, as can be seen from figure 4. During the first period of test runs grinding plates

During the lirst period of test rans general arrays of slots. In

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Experience in the Introduction of Simultaneous Bilateral Grinding of Sheet Glass

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figure 5 the two specimens are shown which meet the requirements. The experimental evidence is presented in a table. It was found that hydraulic and mechanical pulse generators both operate satisfactorily. The mechanical type, however, is more simple, cheaper to produce and shows less wear. As a conclusion it is stated that the grinding of both glass surfaces proceeds with equal intensity and that the simultaneous bilateral grinding offers great advantages. These experiments furnished the required experience for the design of highly efficient continuous grinding machines. There are 5 figures, and 1 table.

Card 2/2

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VEYNBERG, K.L.; KOSSOY, B.S.; HOL'KEE, M.P.; REZNIKOY, M.I.; KADANER, N.I., red., ind-ve; RUDAKOVA, N.I., tekhn. red.

[Equipment for glass plants] Oborudovanie stekol'nykh savodov. Pod red. M.I.Reznikova. Izd.2., ispr. i dop. Hoskva. Gos. izd-vo lit-ry po stroit., arkhit. i stroit. materialsm, 1961. 618 p. (MIRA 14:8)

(Glass manufacture-Equipment and supplies)

VEYNBERG, Kal'men Lipmanovich; GURFINKEL', Isaak Yevgen'yevich[deceased];
KOTLYAR, Abram Yevseysvich; NOL'KEH, Maksimilian Petrovich;
ORLOV, Anatoliy Nikolayevich; KHERSONSKIY, Sergey Semenovich;
SHKOL'NIKOV, Yakov Abramovich; BROMLEY, P.V., retsenzent;
ZALIZNYAK, A.A., retsenzent; KISELEV, N.V., retsenzent; KIEGG,
D.I., retsenzent; SHVAGIREV, Ya.D., retsenzent; DUKHOVNYY, F.N.,
red.; TRISHINA, L.A., tekhn. red.

[Equipment and mechanization of glass factories]Oborudovanie i mekhanizatsiia stekol'nykh zavodov. [By] R.L.Veinberg i dr. Momekhanizatsiia stekol'nykh zavodov. [By] R.L.Veinberg i dr. M

CECH,M.; HOSKOVA,A.; NOLL,A.

Transminase activity in healthy infants and its relation to neonatal jaundice. Cosk. pediat. 20 no.1:23-29 Ja '65

1. I. detska klinika lekarske fakulty University J.E. Purkyne v Brne (prednosta - prof. dr. Z. Brunecky, CSc.)

HOSKOVA, A.; GECH, M.; NOLL, A.

About the possibility of glucose-6 phosphate dehydrogenase deficiency in our country. Cas. lek. cesk. 164 no.10: 262-265 12 Mr*65.

1. I. detaka klinika lekarske fakulty University J.E. Purkyne v Brne (prednosta: prof. dr. Z. Brunecky, CSc.

"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137.

NOLL', I. F.

Grain

Raising high yields of grain crops. Dost. sel'khoz. No. 2, 1953.

Monthly List of Russian Accessions, Library of Congress, June 1953. Uncl.

NOLL, J., inz.

Distribution of fiber circulation during fragmentation. Bul VUPC 6 no. 3: 3-17 163.

1. Research Institute of Paper and Cellulose, Prague.

NOLL, Jaroslav, inz.

Relations and phenomena during paper web formation. Pt. 1. Papir a celulosa 19 no. 7:192-194 Jl '64.

1. Research Institute of Paper and Cellulose, Worksite Prague.

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"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137

MC(), Jaroslav, inz., Fd.823, Fedrich, inz.; VASAK, Jaroslav, inz.

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g celulosa 19 oc.2:253.252 5 low.

1. Repharen institute of Paper and Cellulose, Worksite

Projuc.

NOLL, Jaroslav, inz.

Relations and phenomena in making paper web. Pt.2. Papir a celulosa 19 no.8:219-222 Ag 164.

1. Research Institute of Paper and Cellulose, Worksite Prague.

residente de **S**ector de la compansión d KOVACS, Ervin, dr.,; RAMEY, Erno, dr.,; KERTESZ, Edith, dr.,; HOLL, Kelman, dr. Familial idiopathic hypoconvertinenia (absence of the VII factor) Orv. hetil. 96 no.14:378-383 3 Apr 55. 1. A Kagyar Kephadsereg Egeszsegugyi Szolgalatanak kozlesenye. (HEMORRHAGIC DEATHESIS factor VII deffic., idiopathic, familial)

S/181/61/003/008/017/034 B102/B202

9.4340 AUTHORS:

Nolle, E. L. and Galkin, G. N.

TITLE:

Generation centers in diffusion-type p-n junctions of silicon

Fizika tverdogo tela, v. 3, no. 8, 1961, 2350-2354

TEXT: The reverse current passing through a p-n junction consists of two PERIODICAL: components: the diffusion current and the current caused by generation in the region of space charge of the semiconductor. At room temperature, the diffusion component of the reverse current in silicon p-n junctions is considerably lower than the second component. It is known that in silicon with p-n junctions mainly carriers whose levels lie near the center of the forbidden band are generated in the region of space charge. The authors study the carrier-generation centers in the region of space charge which had been generated by heat treatment in diffusional p-n junctions of silicon and determine the relationship between the generation centers and the recombination levels in p-type silicon. On the basis of Shockley's the recombination levels in p-type silvon. On the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density caused by generation in the space-theory for the reverse-current density of the reverse-current densit

Card 1/3

5/181/61/005/008/017/034 B102/B202

Generation centers in ...

 τ_{p_0} and τ_{n_0} are the lifetimes of the electrons and holes, in a strong p-type and strong n-type semiconductor. The authors experimentally studied the volt-ampere characteristics of the reverse current in p-n junctions produced from thermally treated (1255°C) p-type Si plate In order to reduce the influence of surface effects on the reverse current, the authors chose large diode areas (0.12 cm²); immediately before the measurements the diodes were etched and the characteristics were measured in a vacuum thermostat (10⁻⁵ mm Hg). It was found that up to about 100°C the reverse current is voltage-dependent and mainly a generation current. The activation energy of the generation centers was determined from the slope of the straight line I = f(1/T) and a value of 0.6 ± 0.06 ev was obtained. This corresponds to a position of the energy level of the centers in the middle of the forbidden band. At higher temperatures, the reverse current is determined by the diffusion component (activation energy 1.2 ev). The studies showed that a linear relation exists between the generation current and the concentration of the centers which form a recombination level in p-type silicon, that is at a distance of 0.35 ev from the valence band.

Card 2/5

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S/181/61/003/008/017/034 B102/B202

Generation centers in ...

It can be assumed that in the p-n junctions studied a donor level of gold impurities acts as an active recombination level and an acceptor level of gold as an active generation level in the space charge region. The former is at a distance of 0.55 ev from the valence band, the latter lies in the middle of the forbidden band. Using the date of Bemski the author compares the reverse-current densities theoretically and experimentally. Good agreement was obtained for the individual samples. The carrier concentrations were calculated from the formula $n_1^2 = 1.5 \cdot 10^{33} T^3 \exp(-1.21/kT)$. The authors thank V. S. Vavilov for directing the studies and B. M. Vul, Corresponding Member ASUSSR, for his interest and advice. There are 3 figures, 1 table, and 10 references: 1 Soviet and 9 non-Soviet. The two most important references to English-language publications read as follows: G. Bemski. Phys. Rev. 111, 6, 1515, 1958; D. J. Sandiford. J. Appl. Phys., 30, 12, 1981, 1959.

ASSOCIATION: Fizicheskiy institut im. P. N. Lebedeva AN SSSR Moskva

(Physics Institute imeni P. N. Lebedev AS USSR, Moscow)

SUBMITTED: March 10, 1961

Card 3/3

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S/181/61/003/008/018/034 B102/B202

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Galkin, G. N., Nolle, E. L., and Vavilov, V. S.

AUTHORS: TITLE:

Recombination levels in p-type silicon occurring at high-

temperature treatment

PERIODICAL:

Fizika tverdogo tela, v. 3, no. 8, 1961, 2355-2361

TEXT: Heat treatment of silicon at temperatures above 1200°C leads to a strong increase of the suface recombination rate. The lifetime of the nonequilibrium carriers decreases to values of the order of 1 usec and less. The nature of the recombination centers occurring in this connection has hitherto not been explained. In a previous paper (Galkin, FTT, II, 1, 8, 1960) it was demonstrated that in p-type silicon the dependence of the carrier lifetime on the injection level (with injection levels of 0.005-0.05 ev) corresponds to the Shockley-Read law. The recombination level is at a distance of 0.13 ev from the valence band. At higher injection levels, however, no linear dependence could be observed. Hence the authors assumed that another level participates in recombination. This problem is studied in the present paper. The authors study the dependence

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S/181/61/003/008/018/034 B102/B202

Recombination levels in p-type

of the lifetime on the injection level in a wide range of the injection levels, the position of the recombination levels (generated by heat treatment) in the forbidden band and also their nature. First, they theoretically study recombination by local levels which lie in the forbidden band. They experimentally study the dependence of the lifetime of the non-equilibrium carriers on temperature and injection level in p-type single crystals with p-n junction by the "frequency" method of S. G. Kalashnikov and N. A. Penin (ZhTF, XXV, 1111, 1955). The p-n junction was produced by diffusing phosphor into p-type Si (20 min, 1230°C). This was made in quartz ampuls. Under the same conditions part of the specimens had been previously subjected to heat treatment (30 min - 2hr) in order to increase the concentration of the recombination levels. Ohmic contacts were obtained by melting Ag onto the n-type side and Al onto the p-type side. In order to keep the current which is due to surface generation and which passes through the p-n junction low, the junction area was chosen sufficiently large (0.12 cm²) and etched prior to the measurement. The lifetime was determined between -70 and +185°C and the injection levels between 0.01 and 0.6 ev. The initial carrier lifetime was at 50 usec, resistivity was

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S/181/61/003/008/018/034 B102/B202

Recombination levels in p-type ...

~10 ohm·cm. The ratio between diffusion current and generation current component was determined from the volt-ampere characteristics of the current in forward direction. The characteristics (v = f(log I)) have two linear sections of different slope. The first one (0.26 ev) corretwo linear sections of different slope. The first one (0.26 ev) corretwo linear sections of different slope. The space-charge region, at sponds to the current due to generation in the space-charge region, at higher voltages, current occurs due to diffusion. The majority carrier concentration p_0 was determined from the Hall-emf. It was constantly concentration p_0 was determined from the Hall-emf. It became constant equal to 7.5·10¹⁴ cm⁻³ in the entire temperature range. It became constant after a.2.5 hour heat treatment (within the limits of measurement accuracy) after a.2.5 hour heat treatment (within the limits of measurement accuracy) which indicates a low concentration of the introduced centers. The curves which indicates a low concentration of the introduced centers. The curves which indicates a low concentration of the introduced centers. The curves which indicates a low concentration with annealing times of less than 1.5 hr

were not liner. They corresponded approximately to formula

$$\tau \left(1 + \frac{\Delta n}{p_0}\right) = \left\{\frac{1}{\tau_{01} + \tau_{oot} \frac{\Delta n}{p_0}} + \frac{1}{\tau_{02} + \tau_{oot} \frac{\Delta n}{p_0}}\right\}^{-1}.$$
 (5)

Card 3/5

S/181/61/003/008/018/034 B102/B202

Recombination levels in p-type ...

Card 4/5

An is the concentration of the electrons (minority carriers), p_{o} that of the holes (majority carriers), T the lifetime of the latter; the subscripts o and co refer to an infinitely small or infinitely large injection level, 1 and 2 number the two existing recombination levels. Only with specimens that had been subjected to heat treatment for more than two hours these curves were linear. Heat treatment at temperatures exceeding 1200°C also leads to the generation of two donor-type recombination levels at distances of 0.1-0.2 and 0.35 ± 0.02 ev from the valence band. The concentration of the centers with the level $E_{t2} = 0.35$ ev increases with increasing time of heat treatment so that - in the case of long-lasting heat treatment - recombination by the first level can be neglected. may be explained by the presence of gold atoms in the crystal which, according to Collins et al., form donor levels in p-type Si which are at a distance of 0.35 ± 0.02 ev from the valence band. According to Bemski the gold concentration in Si subjected to heat treatment for 2.5 hours, should The reason of this gold impurity might be the quartz amount to 10¹³ cm⁻³. The authors thank ampul which contained the Si during the heat treatment.

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Recombination levels in p-type ...

S/181/61/003/008/01 /034 B102/B202

B. M. Vul, Corresponding Member AS USSR, and E. I. Adirovich for advice, B. Ya. Yurkov for help. There are 7 figures and 11 references: 4 Soviet and 7 non-Soviet. The three most important references to English-language publications read as follows: M. Lax. Phys. Rev., 119, 1502, 1960; C. B. Collins et al. Phys. Rev., 105, 1168, 1957; G. Bemski. Phys. Rev., 111, 6, 1515, 1958.

ASSOCIATION: Fizicheskiy institut im. P. N. Lebedeva AN SSSR Moskva

(Physics Institute imeni P. N. Lebedev AS USSR, Moscow)

SUBMITTED: March 10, 1961

Card 5/5

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37949 s/181/62/004/005/051/055 B163/B138

AUTHORS:

Nolle, E. L., Malovetskaya, V. M., and Vavilov, V. S.

TITLE:

The effect of oxygen on the life-time of minority carriers

in p-type silicon

PERIODICAL:

Fizika tverdogo tela, v. 4, no. 5, 1962, 1374-1376

TEXT: Single crystals of p-type silicon were obtained by zone melting without a crucible. Very low oxygen content was achieved by zone refinement in a hydrogen atmosphere or in vacuum. In the top part of the single crystal the oxygen concentration was increased by making part of the last passage in an atmosphere of moist hydrogen. The oxygen concentration was determined from the intensity of the infrared absorption band at 9.1 microns. The life-time was measured by B. D. Kopylovskiy's phase method at a low injection level. With oxygen content increasing from 5.10 16 cm -3 to 1.5.10 17 cm -3 the carrier life-time increases from 1.6 to 32 microseconds. Its temperature dependence was measured between 220 and 430°K and was found to diminish with temperature. The decrease is less for specimens with higher oxygen concentrations, and below 0°C, it increased Card 1/2

ACCESSION NR: AF4034920

E/0181/64/006/005/1406/1412

AUTHOR: Vavilov, V. S.; Melle, E. L.; Yegorov, V. D.; Vintukin, S. I.

TITLE: Radiative recombination in cadmium telluride as a result of excitation by fast electron pulses

SOURCE: Fizika tverdogo tela, v. 6, no. 5, 1964, 1406-1412

for the wife between

TOPIC TAGS: radiative recombination, cadmium telluride, CdTe, laser material, stimulated emission, semiconductor

ABSTRACT: The recombination radiation spectrum of CdTe excited by fast electrons was investigated in the photon energy interval from 0.7 to 1.6 ev and at temperatures between 10 and 300K. The p-type samples with resistivity of ~ 10 ohmom were excited by 1 Hev electron pulses of 2.5 usec duration from an electrostatic generator. The repetition frequency was 10 cps, and the current density per electron pulse varied between 0.3 and 0.5 mA/cm. Since a 30 hr exposure to this type of irradiation did not affect the recombination

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ACCESSION NR: AP4034920

radiation spectrum, it was assumed that the effect of the formation of radiation defects could be neglected. It was found that at 10K the recombination radiation spectrum consists of three intense bands with maxima at photon energies of 1.05 ± 01, 1.47 ± 0.01, and 1.59 ± 0.01 ev. The short-wave emission band is located in the region of the fundamental absorption band. Analysis of the data shows that vertical transitions with emission of optical phonons with zero momentum occur in CdTe and that the probability of such processes is high. According to criteria developed in: Basov, N. G., O. N. Krokhin, Yu. H. Popov. ZhETF, v. 4, 1961, p. 1203, it temperatures when the nonequilibrium charge carrier concentration is considerably smaller than that corresponding to the degenerate state. Orig. art. has: 6 figures.

ASSOCIATION: Fizicheskiy institut imeni P. N. Lebedeve AN SSSR (Physics Institute AN SSSR)

Card 2/3

ACCESSION WR: AP4034920
SUBHITTED: 20Nov63 DATE ACQ: 20Kay64 ENCL: 00
SUB CODE: PN NO REF SOV: 004 GTHER: 006

VAVILOV, V.S.; NOLLE, E.L.; YEGOROV, V.D.

Recent data on the spectrum of recombination emission in cadmium telluride following electron excitation. Fiz. tver. tela 7 no.3; 934-936 Mr 165. (MIRA 18:4)

1. Fizicheskiy institut imeni Lebedeva AN SSSR. Moskva 1 Moskovskiy gosudarstvennyy universitet.

EWG(m)/EWP(k)

L 2982-66 \pm EWA(k)/FED/EWT(1)/EWT(m)/EEC(k)-2/ETC/T/EWP(t)/EWP(b)/EMA(m)-2/EMA(h) ACCESSION NR: AP5023360 SCTB/LIP(c) WG/RIM/JD

UR/0020/65/164/001/0073/0074

AUTHOR: Vavilov, V. S.; Nolle, E. L.

Cadmium telluride electron-beam pumped CdTe laser

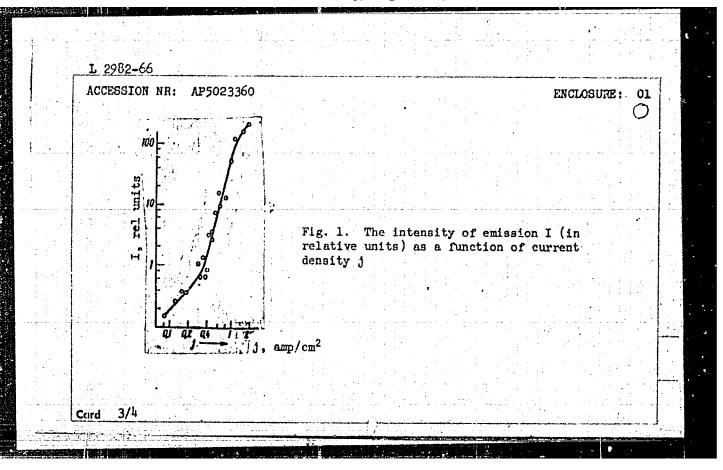
SOURCE: AN SSSR. Doklady, v. 164, no. 1, 1965, 73-74

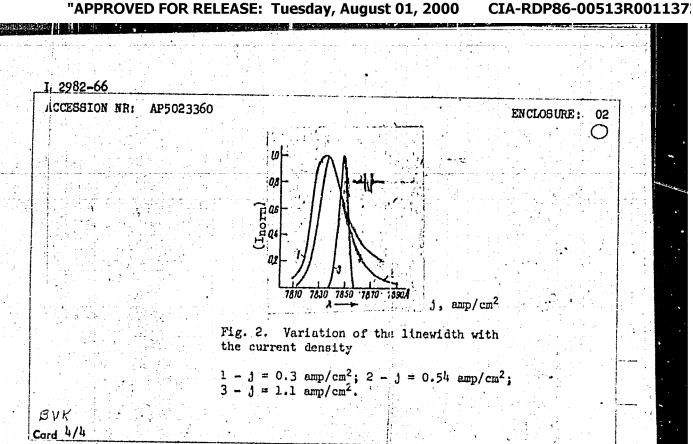
TOPIC TAGS: laser, semiconductor laser, CdTe, electron beam laser, recombination radiation

ABSTRACT: The authors report attaining laser action in CdTe pumped by a beam of electrons. A sample 0.4 x 0.4 x 0.4 mm was cleaved from n-type CdTe with a hole concentration of 10^{14} cm⁻³ at room temperature. The polished front face of the sample was perpendicular to the two polished faces forming the cavity. The sample was attached to the cold finger of a cryostat maintained at 10-15K. beam of 150-kev electrons was incident on the front face of the sample. The team current was supplied in 0.4-usec pulses at a rate of 10 pulses per second. The short-wavelength radiation emitted perpendicular to the polished faces forming the cavity was shifted 20-30 % toward the longer wavelengths, as compared with radiation emitted from the front face exposed to the electron beam. When the current density was increased from 0.3 to 1 amp/cm2, the intensity of emission increased

Card 1/4

L 2982 – 66	The state of the s		
ACCESSION NR: AP5023360			3
by approximately two orders of the width at half maximum decrea current density of 1 amp/cm ² to the front face was about 15° to 300 w, the output power with The narrowing of the spectral 1 intensity, and the appearance o	the divergence in the horiz . At an input power of the din a solid angle of 15° was the to a value less than kT	ontal plane perpen exciting electron not less than 0.3 e, a sharp increase ent density of 1 am	dicular s equal w. in p/cm ²
indicated the onset of stimulat to exciton transitions. Orig. ASSOCIATION: Fizicheskly insti	art. has: 2 figures. tut im. P. N. Lebedeva Akad	ed emission was avo	[CS]
indicated the onset of stimulat to exciton transitions. Orig.	art. has: 2 figures. tut im. P. N. Lebedeva Akad	demii nauk SSSR (Ph	[CS] ysics
indicated the onset of stimulat to exciton transitions. Orig. ASSOCIATION: Fizicheskiy insti Institute, Academy of Sciences,	art. has: 2 figures. tut im. P. N. Lebedeva Akad SSSR)	demii nauk SSSR (Ph	[CS] ysics
indicated the onset of stimulat to exciton transitions. Orig. ASSOCIATION: Fizicheskiy insti Institute, Academy of Sciences, SUBMITTED: 25Jan65	ed emission. The stimulate art. has: 2 figures. tut im. P. N. Lebedeva Akad SSSR)	demii nauk SSSR (Ph	[CS] ysics
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indicated the onset of stimulat to exciton transitions. Orig. ASSOCIATION: Fizicheskiy insti Institute, Academy of Sciences, SUBMITTED: 25Jan65	ed emission. The stimulate art. has: 2 figures. tut im. P. N. Lebedeva Akad SSSR)	demii nauk SSSR (Ph	[CS] ysics





EWI(m)/EIC(f)/EWO(m)/EWP(t) IJP(c) RDW/JD SOURCE CODE: UR/0181/66/008/001/0286/0287 AP6003819 AUTHOR: Nolle, E. L.; Vavilov, V. S.; Golubev, G. P.; Mashtakov, V. S. ORG: Physics Institute im. P. N. Lebedev, AN SSSR, Moscow (Fizicheskiy institut AN SEER) TITLE: Induced radiation of cadmium selenide due to electron excitation SOURCE: Fizika tverdogo tela, v. 8, no. 1, 1966, 286-287 TOPIC TAGS: light radiation, radiation intensity, light emission, light excitation ABSTRACT: An attempt was made to obtain stimulated emission of light from calcium selenide excited with electron pulses. A specimen having the form of a rectangle parallelepiped 600 x 400 x 50 μ was used for observation of the emission. The electron beam was incident on the largest surface of the specimen, while the emission was recorded from the specimen's side faces, the distance between which was 600 µ. The measurements were made at 80K. The observation of emission from the side faces showed that the maximum of the spectral band is shifted by 35 Å to the longwave side as compared with emission recorded from the forward face irradiated with electrons. When current density was increased from 1 amp/cm2, a sharp increase in emission intensity was observed along with the simultaneous appearance of the directional effect of emission and a decrease of the width at the half-height of the band from 80 to 15 Å. At a current density of 2.5 amp/cm2, the emission spectrum has an equidistant struc-Z Card 1/2

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IJP(c) L 21477-66 EWT(1)/EWT(m)/EWG(m)/EWP(t) RDW/JD/AT SOURCE CODE: UR/0181/66/008/002/0532/0540 ACC NR: AP6006842 Vavilov, V. S.; Nolle, E. L. AUTHOR: Physics Institute im. P. N. Lebedev, AN SSSR, Hoscow (Pizicheskiy いいいからいにはなる 大変なで 人間ののないないのは、日本ので、日本ので、日本のではないののではない。 でんちょうかいかん institut AN SSSR) Spontaneous and stimulated emission of recombination radiation of CdTe due to electron excitation 21,444, 455 40 39 SOURCE: Fizika tverdogo tela, v. 8, no. 2, 1966, 532-540 B TOPIC TAGS: recombination radiation, recombination emission, single crystal ABSTRACT: An investigation was made of the emission of recombination radiation by nonalloyed single CdTa crystals due to excitation by 150-kev electrons. An electron tube with a constant high voltage which generated 150-kev electron pulses with a duration time from 0.25 to 10 usec was used. A beam of electrons was focused on a spot 1 mm in diameter, where the current density reached 3 amp/cm2. The free path of 150-kev electrons in CdTe was about 40 µ. The emission spectrum of CdTe due to electron excitation consisted basically of four bands with photon energies close to 1, 1.4, 1.55, and 1.59 ev at T = 10K. It was possible that the emission bands at 1 and 1.55 ev in CdTe not Card 1/2

1

L 21477-66 ACC NR: AP6006842 alloyed with impurities were associated with recombination through single- and double-charged acceptor vacancies of cadmium, whose energy levels are $E_{\rm V}$ + 0.05 and $E_{\rm C}$ - 0.6 eV, respectively. The emission band at 1.47 ev could be associated with recombination through foreign impurities. The intensity of the shortwave exponentially with the temperature decrease I \sim T-n, where n = 0.5-1.5, thus indicating the absence of a thermal barrier. The intensity of the band also increased with the excitation level according to the square law. At high excitation levels the intensity dependence changed into a linear one in the case of the highest-purity CdTe specimens, thus indicating the predominance of radiation emission recombination. Apparently, the shortwave emission band was linked with the annihilation of excitons. A direct coherent stimulated radiation emission of CdTe was observed in a region corresponding to the annihilation of excitons at a current density exceeding 0.3 amp/cm2 for 10K and 1 amp/cm2 for 80K. Orig. art. has: 1 formula and 8 figures. [JA] SUB CODE: 20/ SUBM DATE: 11May65/ ORIG REF: 011/ OTH REF: 010 ATD: PRESS: 4218

32642-66 EWT(1)/EWP(0)/EMT(m)/EMP(t)/ETI IUP(2) JD/WH 48. AP6015473 (A) SOURCE CODE: UR/0181/66/008/005/1522/1527 (A) ACC NR. AP6015473 AUTHOR: Vavilov, V. S.; Golubev, G. P.; Konorova, Ye. A.; Holle, E. L.; Sergiyenko, 53 ORG: Physics Institute im. T. N. Lebedev AN SSSR, Hoscow (Fizicheskiy institut AN A SSSR) TITLE: Recombination radiation of diamonds during excitation by electrons SOURCE: Fizika tverdogo tela, v. 8, no. 5, 1966, 1522-1527 TOPIC TAGS: recombination radiation, diamond, excitation spectrum, electron beam ABSTRACT: The authors study the recombination radiation spectrum of a diamond near the fundamental absorption edge and in the visibl region. A pulsed beam of 150 kev electrons was used for excitation. The pulse duration was variable from 1.3 to 12 usec with a prr of 10 cps. The current density in the beam could be raised to 2 a/cm2 The recombination radiation spectrum extended in the visible region from 580 to 320 mu. Some specimens showed a narrow band with a maximum at 389 mu. The radiation spectrum in the ultraviolet region consists of three bands with maxima at 235, 242.3, and 250 mm. The integral intensity of the fundamental radiation band (maximum 235 mm) is only 0.5-1% of the integral radiation intensity in the visible region. It is assumed that the bands at 242.3 and 250 mm are phonon repetitions of the band at 235 mm. Card 1/2

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When the curve for this band is extended along the axis for phonon energy is pears asymmetric with a form approaching Maxwell distribution, which indicates the the radiation is due to recombination of free particles. The shape and position the ultraviolet radiation bands, and the effect of excitation level and temperate on luminescence intensity show that luminescence is caused by annihilation of extens with simultaneous radiation of phonons. Orig. art. has: 5 figures, 3 tables.								
	SUB CODE:	20/	SUBM DATE:	210ct65/	OTH REF: 006/	ATD PRESS:5025	5	

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APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R0011373

ENT(1)/T IJP(c)=AT L 40050-66 SOURCE CODE: UR/0120/66/000/003/0176/0179 ACC NR. AP6022024 AUTHOR: Vavilov, V. S.; Nolle, E. L.; Yegorov, V. D.; Golubev, G. P.; Mashtakov, V. S. ORG: Institute of Physics, AN SSSR, Moscow (Fizicheskiy institut AN SSSR) TITLE: Outfit for studying the recombination radiation of electron-excited semiconductors ? SOURCE: Pribory i tekhnika eksperimenta, no. 3, 1966, 176-179 TOPIC TAGS: semiconductor research, recombination radiation ABSTRACT: Connected with the outfits described by C. Benoit et al. (Physics of Semiconductors, Paris, Dunod, 1964), an improved outfit developed by the authors is capable of exciting semiconductors by 150-kev electron pulses that have a current density of 3 amp/cm²; pulse duration, 0.25--10 resc; repetition rate, up to 30 cps. Stimulated radiation of cadmium telluride was achieved in this outfit for the first time. An electron tube with a constant high voltage and a pulsed grid modulation is used for high-power electron excitation of semiconductors; a 20-section steatite tube has been actually used. A block diagram of the outfit, principal circuits of the pulse generator and synchronous detector, and the pulse shape of the electron beam are shown. A He cryostat permits studying the recombination radiation of semiconductors at temperatures down to 10K. "The authors wish to thank S. I. Vintovkin, V. S. Ivanov, and B. D. Kopylovskiy for their valuable advice connected with the development of the outfit." Orig. art. has: 4 figures. SUB CODE: 20, 09 / SUBM DATE: 25Nay65 / ORIG REF: 004 / OTH REF: 002 UDC: 539.293

"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137

ACC NR: AP7005333

SOURCE CODE: UR/0181/67/009/001/0122/0128

AUTHOR: Nolle, E. L.

ONG: Physics Institute im. P. N. Lebedev, AN SSSR, Moscow (Fizicheskiy institut AN

SSSR)

TITLE: Recombination via exciton states in semiconductors

SOURCE: Fizika tverdogo tela, v. 9, no. 1, 1967, 122-128

TOPIC TAGS: semiconductor carrier, exciton, radiative recombination, electron recombination, stimulated emission, impurity center

ARSTRACT: The purpose of the study was to clarify the role of excitons in the recombination of electrons and holes in semiconductors by analyzing the statistics of recombination via exciton states. A relation is derived between the exciton binding and dissociation coefficients and an equation obtained for the recombination rate with account taken of the additional recombination via impurity centers and of the radiative interband recombination. It is shown that the rate of recombination via exciton states can exceed the rate of interband radiative recombination at values of kT both higher and lower than the exciton binding energy. Various recombination parameters (forbidden band width, exciton lifetime, binding coefficient, and ratio of exciton and interband recombination) are estimated for a number of semiconductors (Ge, Si, GaAs, CdTe, CdS, ZnS). The stimulated emission from semiconductors in the presence of exciton states and the statistics of recombination with account taken of

Card 1/2

UDC: none

ACC NR: AP7005333

capture of the exciton by impurity centers is also discussed. It is shown that for the most part the conditions for stimulated emission are not satisfied in the presence of exciton states. In the case of low excitation level, the recombination rates of captured and of free excitons follow the bimolecular law. Under certain conditions, the recombination rate of the captured excitons may exceed that of the free electrons. The author thanks V. S. Vavilov for interest in the work and B. M. Vul, Yu. A. Kurskiy, M. V. Fok, and V. A. Chuyenkov for a discussion of the results. Orig. art. has: 2 figures, 15 formulas, and 1 table.

SUB CODE: 20/ SUBM DATE: 30May66/ ORIG REF: 009/ OTH REF: 010/ ATD PRESS: 5116

Card 2/2

HOLLE, L.I.

Clinical aspects and therapy of toxic forms of Filatov's disease (acute mononucleosis). Elin. med., Moskva no. 4:48-51 Ap 150.

(GIML 19:3)

1. Rige.

NOTIF, L. YA

22717 Holle, L. Ya Klinicheskoye Znacheniye Vitamina K Pri Krovotecheniyakh Yazvennoi Oopezni I Khirurgicheskikh Operatsiyakh. Zdravookhranehniy Sov Patv, So. Z, 1949, S. 62-72.: Rezyumee Na Patysh. Yaz.

SO: Letopis', No. 30, 1949

NOLLE, L. Ya.

Polyarthritis syndrome in the pre-ictoric period of Botkin's disease. Klin. med., Moskva 29 no.7:52-55 July 1951. (CLHL 20:11)

1. Candidate Medical Sciences. 2. Riga.

MOLLE L. L. kandidat meditsinskikh nauk (Higa); LAZAHEVA, M.S. (Riga); MATS, Ye.I. (Riga) Valdman's test in Botkin's disease. Klin.med. 32 no.3:81 Mr *54. (NURA 7:5) (Hepatitis, Infectious)

NOYLE, L.Ya., kand.med.nauk; SHTERMBERG, D.B., kand.med.nauk

Gandidomycosis of the internal organs. Sov.med. 22 no.3:92-99
Nr '58.

1. Is patologoanatomicheskogo otdelaniya (zav. - prof. Ye.Ya.
Gertaenberg) 6-y Gorodskoy klinicheskoy bol'nitsy (glavnyy vrach
H.S.Shevyakov) Hosky.

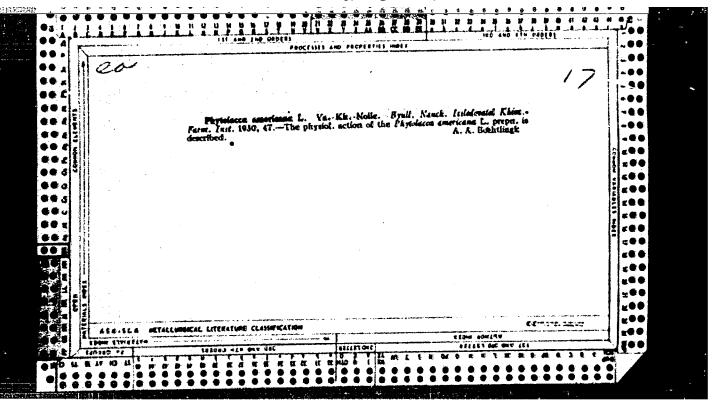
(MONILLASIS, etfol. & pathogen.

internal organs, caused by antibiotic ther. (Rus))

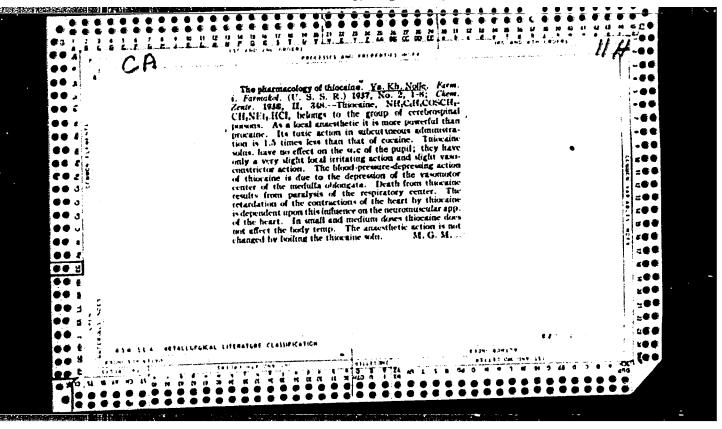
(AITEBIOTICS, inj. eff.

moniliasis of internal organs (Rus))

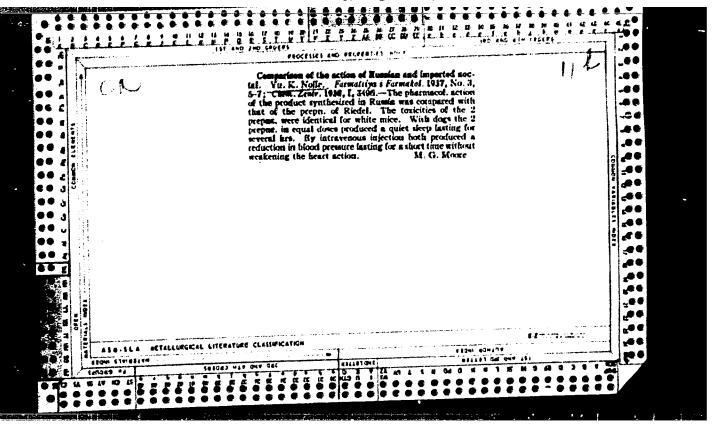
"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137.



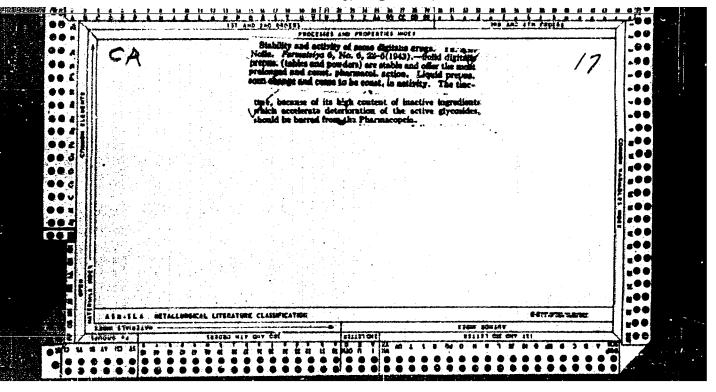
"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137



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- 1. HOLLE, YA. KH.
- 2. SSSR (600)
- 4. Valerian
- 7. Biological method of evaluating valerian preparations. Apt. delo No. 2, 1952

9. Monthly List of Russian Accessions, Library of Congress, February 1953, Unclassified.

BELOVA. O.I.; HOLLE, Ya. Kh., professor, savedujushchiy farmakologicheskoy laboratoriyey; KUTUNOVA. We.E., direktor, savedujushchaya Tsentral nym nauchno-iseledovatel skim apiechsym institutom.

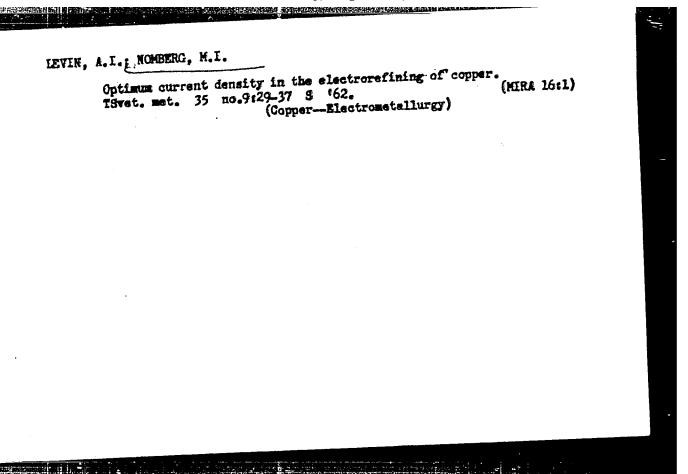
Liquid extract of Magnolia grandiflors as a new drug. Apt.delo 2 no.2:65-66 Mr-Ap 153.

1. Farmskologicheskaya laboratoriya Tsentral'nogq nauchno-issledovatel'skogo aptechnogo instituta Kinisterstva sdravookhraneniya ESFSR. (Magnolia) (Hypertension) (Drugs)

LEVIN, A.I.; LETSKIKH, Ye.S.; MIKHIN, V.A.; NOMBERG, M.I.

Belance of cell voltage and ways to economise electric power in the electrorefining of copper. Isv.Vys. ucheb. sav.; tevet. met. 5 no.1: (22-71 '62.

1. Ural'skiy politekhnichaskiy institut, kafedra tekhnologii elecktrokhimichaskikh proizvodstv. (Copper—Electrometallurgy)



LEVIN, A.I.; LETSKIKH, Ye.S.; MUKHIN, V.A.; HOMBERG, M.I. Balance of bath voltage and ways to improve the operation of electrolytic cells in copper electrolysis plants. TSvet. met.

(MIRA 15:11)

35 no.11:52-57 N '62. (Copper-Electrometallurgy)

"APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R001137.

Nomerov, B.A.

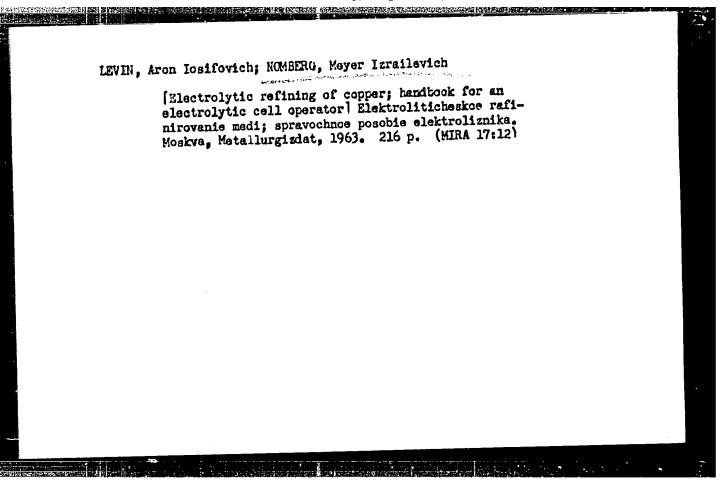
Some methods of calecting ross caedings according to market physiological indices. Nauch.dokl.vys.ahkoly; biol.nauki no.4:193-195 165.

1. Rekomendovana Botanicheskin sadom Moskovskogo gosudarstvennogo universiteta im. N.V.Lomonosova.

NOMEROV, Boris Aleksandrovich; POMALEN KAYA, O.T., red.; GEORGIYEVA, G.I., tekhn, red. [Gulture and varieties of roses in Moscow Province]Kul'ture i sorte ros Moskovskoi oblasti. Moskva, Isd-vo Mosk. univ., (MIRA 16:2) 1962. 192 p.
(Moscow Province—Roses)

NOMEROV, Boris Aleksandrovich; POMALEN KAYA, O.T., red.

[Cultivation of roses in the central zone of the U.S.S.R.]
Kultura roz v srednei polose SSSR. 2. dop. izd. Moskva,
Izd-vo Mosk. univ., 1965. 220 p. (MIRA 18:7)



NOMEROV, B.A.

Fruit setting in selecting different parental pairs of roses.

Vest. Mosk. un. Ser. 6: Biol., pochv. 18 no.5:48-50 S-0 '63.

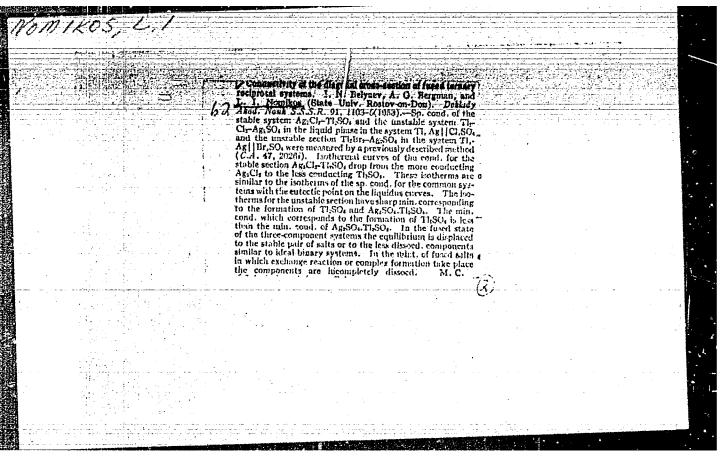
(MIRA 16:10)

1. Botanicheskiy sad Moskovskogo universiteta.

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CIA-RDP86-00513R001137



KRYUKOV, P.A.; NOMIKOS, L.I.; AVGUSTINSKIY, V.L.; POGOREL'SKIY, N.S.

Rock solutions in the region of the Caucasian mineral waters.

Dokl. AN SSSR 157 no.5:1118-1120 Ag *64. (MIRA 17:9)

1. Institut neorganicheskoy khimii Sibirskogo otdeleniya AN SSSR. Predstavleno akademikom A.P. Vinogradovym.

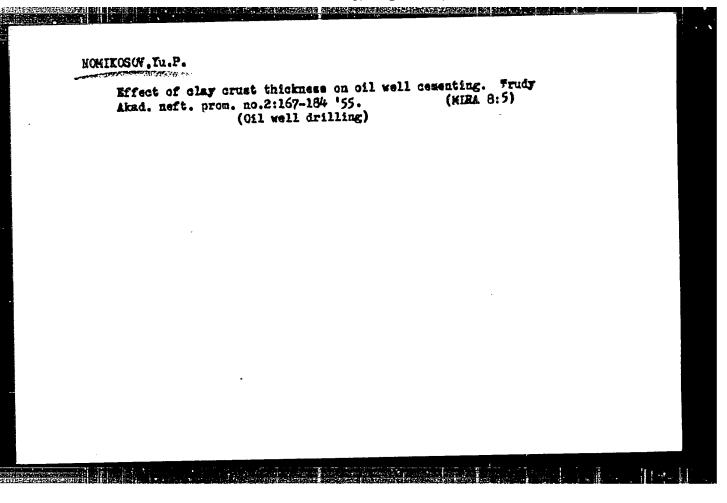
Significance of the pH value in mercurimetric determination of chierrae ions. Gidrekhim.mat.24:51-52 '55. (KERA 9:4)

1.Gidrekhimicheskiy institut Akademii nauk SSSR, g. Hevecherkassk.
(Water, Undergreund) (Water-Analysis)

MOMINOS, L.I.; IMMOPIK, I.Ya.; KRYUKOV, P.A. Colorimetric determination of magnesium with titan yellow. (MIRA 9:4) Gidrekhim.mat.24:52-55 155. 1.Gidrekhimicheskiy institut Akademii nauk SSSR, g. Nove-

cherkassk.

(Water, Underground) (Water-Analysis)



NOMIKOSOV, Yu. P. Moscow Order of Labor Red Banner Petroleum Inst imeni Academician I. M. Gubkin

NOMIKOSOV, Yu. P.- "Some problems of increasing the quality of cementing of oil wells."

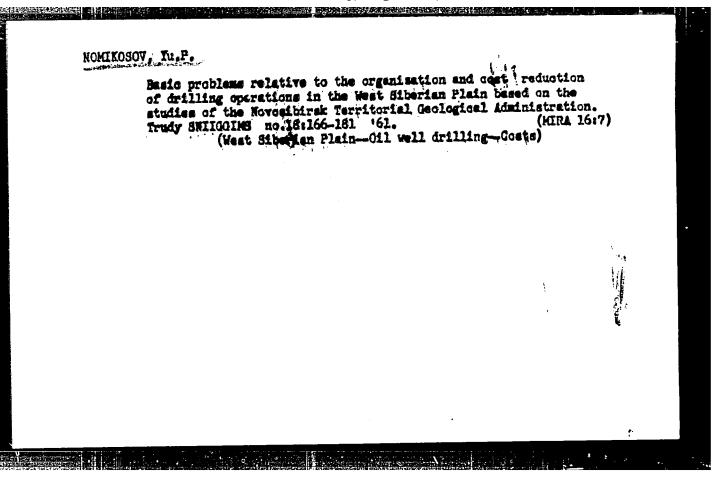
Moscow Order of Labor Red Banner Petroleum Inst imeni Academician I. M. Gubkin.

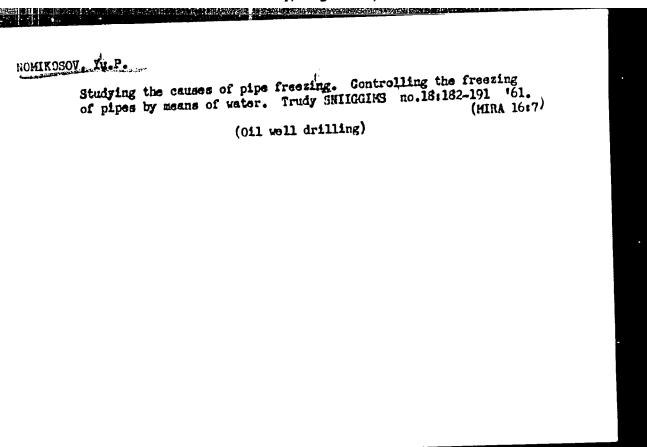
Moscow, 1956.

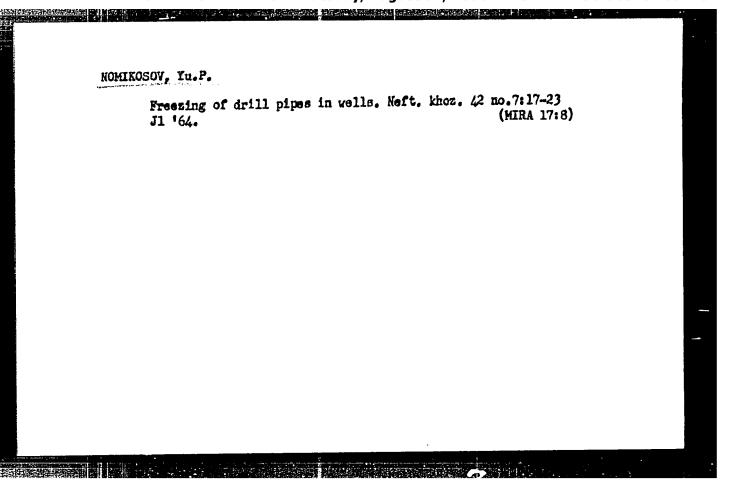
(Dissertation for the Degree of Candidate in Technical Sciences.)

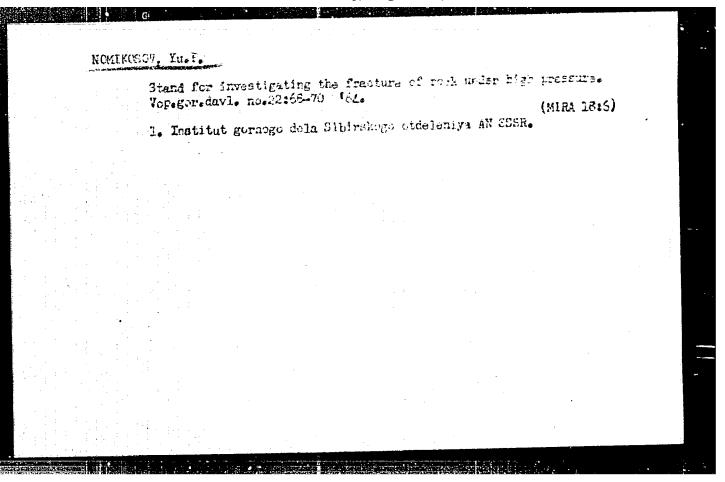
SO: Knizhnaya Letopis' No. 13, 1956.

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CIA-RDP86-00513R001137

R-3

Nomm

USSR/Diseases of Farm Animals - Diseases Caused by Viruses

and Rickettsiae.

: Ref Zhur - Biol., No 14, 1958, 64649 Abs Jour

Author

: Norm, E.

Inst Title

On Infectious Anemic in Horses and on Measures for

Preventing It.

: Eesti Pollumaj. Akad. teaduslike toode kogumik; Sb. Orig Pub

nauchn. tr. Est. s.-kh. akad., 1957, 3, 268-277.

Abstract : No abstract.

Card 1/1

- 14 -

[Nomma, E.]; SAPOCOV, A.G.; SAPAROV, S.; SHAKHMARDANOV, Z.A., kand reter hank; GRITSENYUK, N.

Throughout the Soviet Union. Veterinariia 37 no.1:94-96 Ja '60. (MIRA 16:6) (Veterinary medicine) (Kovalev, Saveli Leonovich, 1911-1959)

NORM, Evald, dots., kond. veter. nauk; AVARSOO, H., red.; TONISSON, A., tekhn. red.

[Organization of veterinary medicine]Veterinaarorganisatsicon.
Tallinn, Eesti riiklik kirjastus, 1961. 247 p. (MIRA 15:5)

(Veterinary medicine)

NOMM, L.

Preliminary data on dusting seed clover with DDT. p.452 SOTSIALISTLIK POLLUMAJANDUS. Tallinn, Estonia. Vol. 14, no. 10, May 1959

Monthly List of East European Accessions (EFAI), LC. Vol. 8, No. 9, September 1959 Uncl.

NomoFilor, A.A.

20-6-12/42

AUTHORS:

Bannik, B. P., Kopylova, D. K., Nomofilov, A.A.;

TITLE:

Capture of a K-Meson With Emission of AH2 (Zakhvat K-me-

zona s ispuskaniyem AHe5)

PERIODICAL:

Doklady AN SSSR, 1957, Vol.116, Nr 6, pp. 939-942 (USSR)

ABSTRACT:

The capture of a K-meson with subsequent emission of a He2 hyper-fragment was found in a stack of photoemulsions irradiated in great hight. This capture is illustrated in a sketch. The particle entered the stack from outside, passed over a distance of 27,3 mm in the emulsion and subsequently stoped by producing a d-star. Both from the range and the scattering of the particle $m = (823 \pm 160)$ m_e was found for the mass of the particle and from the ionization measurings resulted m = 700 m_e. Apparently a K-meson is concerned. A black trace of this star ends with a further star from which a pion is emitted. The second star occured apparently with the decay of the stoped hyper-fragment into three charged particles. Each of these particles has the charge Z \ 2. The scheme of decay of this star has the form ΛHe² - He⁴ + p + π. The kinetic energy of the decay products amounts to $Q_k = (34, 2 + 0.4)$ MeV. The total of the momenta of the formed particles p = (15 + 26) MeV/c. With this decay also the formed particles a neutron with very little energy could be emitted. In this case the scheme of decay would be as follows: AHe2 - He2 + p + n +

Card 1/2

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Capture of a K-Meson With Emission of MH2.

20-6-12/42

 $+\pi^{-}$. The subsequently discussed cinematic analysis of the primary star allows a more precise indentification of the hyper--fragment.F. In this case all possible combinations from 2,3,4 and 5 particles of the primary star are taken into consideration. It is not impossible that the hyperfragment can sometimes be formed in excited state and then by emission of a r- quantum passes over into the ground state. In the concrete case investigated here, two combinations of particles are possible for which the binding energy B assumes none-negative values: 1st combination: AH2 and p occurred with the decay of the excited hyperfragment AL126. The binding energy amounts to BA = (2,2 + 0,7) MeV. The energy of the proton amounts to $E_{\rm p} = (10, 6 \pm 0, 2)$ MeV in the center-of-gravity system. 2nd combination: AH3 and n were formed with the decay of the excited hyper-fragment ALT. The binding energy amounts to BA = (-0,9++2,0)MeV. The energy of the neutron in the center-of-gravity system amounts to En= (9,9+1,1)MeV. There are 1 figure, 1 table, and 4 non-Slavic references.
ASSOCIATION: / Institute of Nuclear Research(Ob"yedinennyy institut yadernykh

PRESENTED:

SUBMITTED: AVAILABLE: Card 2/2

June 1,1957, by N.N.Bogolyubov, Academician

May 25, 1957 Library of Congress

APPROVED FOR RELEASE: Tuesday, August 01, 2000

CIA-RDP86-00513R0011373

Nomofilar A.A.

AUTHORS:

Bannik, B. P., Gulyamov, U. G., Kopylova, D. K., 56-2-3/51

Homofilov. A. A., Podgoretskiy, H. I., Rakhimbayev,

B. G., Usmanova, M.

TITLE:

Hyperfragments in Nuclear Emulsions (Giperfragmenty v

yadernykh emul'siyakh)

PERIODICAL:

Zhurnal Eksperimental'noy i Teoreticheskoy Fiziki, 1958,

Vol 34, Nr 2, pp 286-297 (USSR)

ABSTRACT:

The present work investigates the properties and the relative

frequency of the production of hyperfragments in two

emulsion chambers, which are exposed to cosmic irradiation in the stratosphere. One of the chambers consisted of 600 µ thick emulsion layers of the Ilford type (Il'ford) G-5 and had been irradiated during the international expedition in the Po plains, the second chamber consisted of HMKOM layers of the P type (thickness 400 μ) and was irradiated in the Soviet Union. In this investigation shortly discussed here 67-mesons, 17-meson, 10-particle, 4 K-mesons, 15-hyperon and 5 hyperfragments (of which 5 decayed with the emission of one pion) were found. Not one decay of a 2+-hyperon or of a K+-meson was found, because the method used for

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Hyperfragments in Nuclear Emulsions

56-2-3/51

investigating the emulsion layers excluded the determination of such particles. In all cases the traces of secondary pions were coplanar within 2-3°. The decay of a particle with the mass (860 + 50)me is shown by means of a diagram; this is obviously the decay $\mathcal{I} \rightarrow \pi^+ + \pi^0 + \pi^0$ with the subsequent decay $\pi^0 \rightarrow \gamma + e^+ + e^-$. The mass of the K-meson was determined from the multiple scattering as well as from the remaining range and amounted to (1100 ± 250)me. One of the particles developing in the five-membered star causes a small secondary destruction. With all possible variants of nuclear capture the total energy output is considerably greater than mmc2. The same applies to two of the three other σ_{K} -stars, too. Obviously all σ_{K} -stars found here developed in capturing K-mesons in the light nuclei of the emulsion. In the present work 10 hyperfragments were found which correspond to the criteria suggested by A. Filipkovskiy et al. (ref. 7). (Of these 10 hyperfragments five ended by mesonless decay, the remaining 5 by mesonic decay). For these processes decay the following decay schemes are proposed: $\Lambda \text{He}_2^2 \rightarrow \text{He}_2^2 + p + \pi^-, \Lambda \text{He}_2^2 \rightarrow \text{He}_2^2 \rightarrow \text{He}_2^2 + p + \pi^-, \Lambda \text{He}_2^2 \rightarrow \text{He$

Card 2/3

Hyperfragments in Nuclear Emulsions

56-2-3/51

+ n + π^- . There are 4 figures, 3 tables, and 17 references,

5 of which are Slavic.

ASSOCIATION: United Institute for Nuclear Research (Ob"yedinennyy

institut yadernykh issledovaniy) Tashkent Physicotechnical Institute (Tashkentskiy fiziko-tekhnicheskiy

institut)

SUBMITTED:

July 12, 1957

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1. Nuclear emulsions-Hyperfragments determination

Card 3/3

AUTHOR:

Nomofilov. A. A.

20-1-15/58

TITLE:

7'-Meson Decay With the Creation of an Electron-Positron Pair (Voznozhnyy sluchay raspada 7'-mezona s vyletom elektronno-pozitronnoy pary).

PERIODICAL:

Doklady AN SSSR 1958, Vol. 118, Nr 1, pp. 59-60 (USSR)

ABSTRACT:

Card 1/2

7'-Keson Decay With the Creation of an Electron-Positron Pair. 20-1-15/58

print of a work of Levi-Setti and Slater in which an analogous

case was described.

There are 1 table, 1 figure, and 7 references.

United Institute for Nuclear Research ASSOCIATION:

(Ob"yedinennyy institut yadernykh issledovaniy).

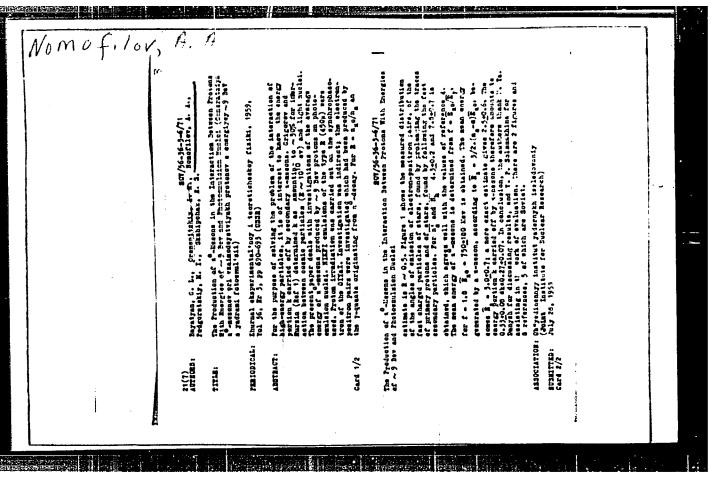
June 6, 1957, by N. N. Bogolyubov, Academician. PRESENTED:

June 1, 1957 SUBMITTED:

Library of Congress AVAILABLE:

Card 2/2

APPROVED FOR RELEASE: Tuesday, August 01, 2000 CIA-RDP86-00513R0011373



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VAN SHU-PEN: [Wang-Shu-fên]; VISHKI, T.; GRAMEMITSKIY, I.M.; GRISHIM, V.G.;
DALKHAZHAY, N.; LEBEDEY, R.M.; KOMOFILOY, A.L.; FODOGRETSKIY, N.I.;
STREEL'TSOV, V.M.

Inclastic interactions between 9 Bev protons and nucleons. Zhureksp. i teor. fis. 39 no.4:957-960 0 160. (NIRA 13:11)

1. Obsycdimenacy institut yadernykh issledovaniy.

(Particles (Muclear physics))

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Mikhaylina, K. M., Nomofilov. A. A., Romanova, T. A., Sviridov, V. A., Tikhomirov, F. A., Tolstov, K. D. AUTHORS !

TITLE:

Interaction of 14.1-Mew neutrons with Li6 and Li7

SOURCE:

Krupchitskiy, P. A., ed. Neytronnaya fizika; sbornik statey.

Moscow, 1961, 249 - 257

TEXT: Interaction of 14.1-Kev neutrons with Li and Li nuclei was studied both with targets prepared from Ilford E, photoemulsions bearing the lithium and with targets of metallic lithium isotopes. The latter method was used for small angles of the departing particles. The mean number of Li nuclei in the photoemulsion was 2.3.10 9 cm⁻². The integral neutron flux striking the emulsion at right angles was about 108 cm-2. Altogether, 412 events were recorded on a 2.5 cm area. 96 events were from the reaction Li⁶(n,t) α with a cross section $\sigma = 27 \pm 6$ mb. Seven Li⁶(n,p)He⁶ reactions with a cross section of about 5 mb were found, moreover Card 1/2

VISHKI, T.; GRAMENITSKII, I.M.; KORBEL, Z.; NOMOFILOV, A.A.; PODGORETSKIY, M.I.; ROB, L.; STREL THOV, V.N.; TUVDENDORZH, D.; KHVASTUNOV, M.S.

Inelastic interactions between protons and nucleons at an energy of 9 Bev. Zhur.eksp.i teor.fiz. 41 no.4:1069-1075 0 '61. (MIRA 14:10)

1. Obayedinennyy institut yadernykh issledovaniy. (Protons) (Mucleons)